## **DESCRIPTION**

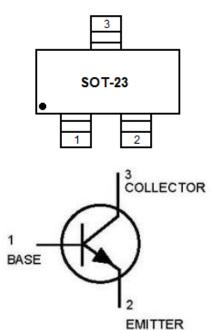
## **FEATURES**

The MBT5550~MBT5551 are available in SOT-23 ● Available in SOT-23 package package.

## ORDERING INFORMATION

Package Type	Part Number	
COT 22	MBT5550	
SOT-23	MBT5551	
Note	SPQ: 3,000pcs/Reel	
AiT provides all RoHS Compliant Products		

## PIN DESCRIPTION



## **ABSOLUTE MAXIMUM RATINGS**

V <sub>CEO</sub> , Collector-Emitter Voltage	140Vdc
V <sub>CBO</sub> , Collector-Base Voltage	160Vdc
V <sub>EBO</sub> , Emitter-Base Voltage	6.0Vdc
Ic, Collector Current-Continuous	600mAdc

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Total Device Dissipation FR-5 BoardNOTE1			
T <sub>A</sub> = 25°C	$P_D$	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	Reja	556	°C/W
Total Device Dissipation Alumina Substrate, NOTE2			
T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	Reja	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

NOTE1: FR-5 = 1.0 x 0.75 x 0.062 in.

NOTE2: Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

REV1.0 - SEP 2020 RELEASED - - 2 -

# **ELECTRICAL CHARACTERISTICS**

T<sub>A</sub> = 25°C, unless otherwise noted

Parameter	Symbol	Conditions	Conditions		Max	Unit
OFFCHARACTERISTICS						
Collector–Emitter		L = 4.0 ··· A d= L = 0	MBT5550	140	-	N/II
Breakdown Voltage <sup>NOTE3</sup>	V (BR)CEO	$I_C = 1.0 \text{mAdc}, I_B = 0$	MBT5551	160	-	Vdc
Collector-Base	V	L = 100uAdo L = 0	MBT5550	160	-	\/da
Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 100μAdc, I <sub>E</sub> = 0	MBT5551	180	-	Vdc
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	$I_E = 10\mu Adc$ , $I_C = 0$		6.0	-	Vdc
		V <sub>CB</sub> = 100Vdc, I <sub>E</sub> = 0	MBT5550	-	100	n A do
Collector Cutoff Current		V <sub>CB</sub> = 120Vdc, I <sub>E</sub> = 0	MBT5551		50	nAdc
	Ісво	$V_{CB} = 100 V dc, I_E = 0,$ $T_A = 100^{\circ} C$	MBT5550	-	100	
		V <sub>CB</sub> = 120Vdc, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C	MBT5551		50	μAdc
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 4.0Vdc, I <sub>C</sub> = 0		-	100	nAdc
ON CHARACTERISTICS						
		I <sub>C</sub> = 1.0mAdc,	MBT5550	60	-	
		V <sub>CE</sub> = 5.0Vdc	MBT5551	80	-	
D0.0 1.0 :	h <sub>FE</sub>	I <sub>C</sub> = 10mAdc,	MBT5550	60	250	_
DC Current Gain		V <sub>CE</sub> = 5.0Vdc	MBT5551	80	250	
		I <sub>C</sub> = 50mAdc,	MBT5550	20	-	
		V <sub>CE</sub> = 5.0Vdc	MBT5551	30	-	
Collector-Emitter	V <sub>CE(sat)</sub>	$I_C = 10$ mAdc, $I_B = 1.0$ mAdc	Both Types	-	0.15	\/da
Saturation Voltage		I <sub>C</sub> = 50mAdc,	MBT5550	-	0.25	Vdc
		I <sub>B</sub> = 5.0mAdc	MBT5551	-	0.20	
Base-Emitter Saturation		$I_C$ = 10mAdc, $I_B$ = 1.0mAdc	Both Types	_	1.0	\/-!-
Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 50mAdc,	MBT5550	-	1.2	Vdc
		$I_B = 5.0 \text{mAdc}$	MBT5551	-	1.0	

NOTE3: Pulse Test: Pulse Width <300  $\mu$ s, Duty Cycle <2.0%.

REV1.0 - SEP 2020 RELEASED - - 3 -

#### TYPICAL CHARACTERISTICS

Figure 1. DC Current Gain

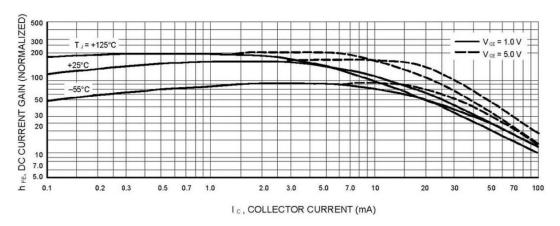


Figure 2. Collector Saturation Region

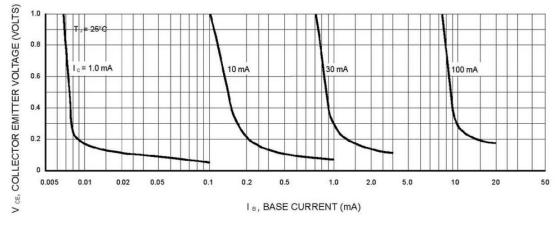


Figure 3.Collector Cut-Off Region

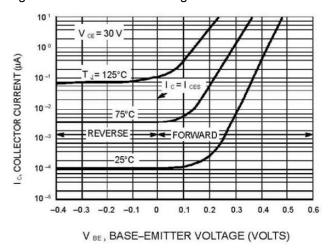
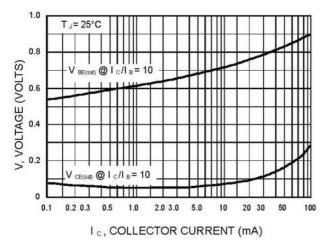


Figure 4. "On" Voltages



REV1.0 - SEP 2020 RELEASED - - 4 -

#### Figure 5.Temperature Coefficients

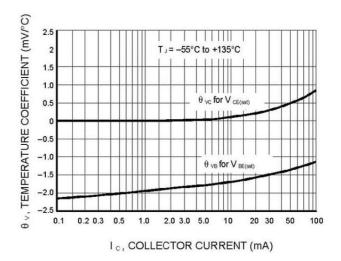


Figure 7. Capacitances

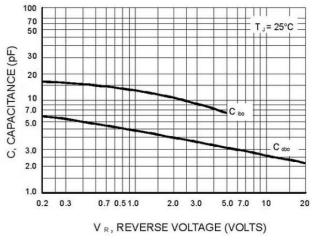


Figure 9. Turn - Off Time

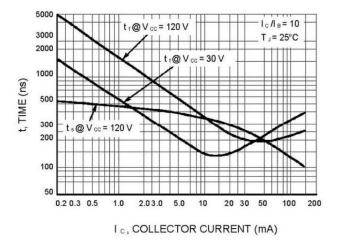
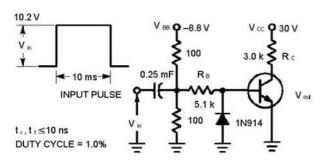
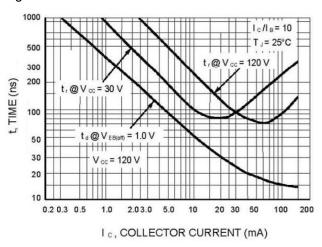


Figure 6. Switching Time Test Circuit



Values Shown are for I c @ 10 mA

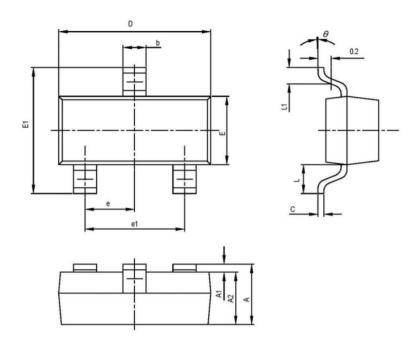
Figure 8. Turn-On Time



REV1.0 - SEP 2020 RELEASED - - 5 -

# PACKAGE INFORMATION

Dimension in SOT-23 Package (Unit: mm)



DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.100	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	'TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

REV1.0 - SEP 2020 RELEASED - - 6 -





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REV1.0 - SEP 2020 RELEASED - - 7